

March 2009

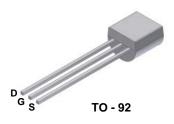
### BS170 / MMBF170 N-Channel Enhancement Mode Field Effect Transistor

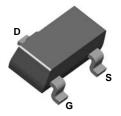
#### **General Description**

These N-Channel enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. They can be used in most applications requiring up to 500mA DC. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

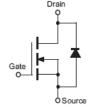
### **Features**

- High density cell design for low R<sub>DS(ON)</sub>.
- Voltage controlled small signal switch.
- Rugged and reliable.
- High saturation current capability.





**SOT - 23** 



Absolute Maximum Ratings T<sub>a</sub> = 25°C unless otherwise noted

	<b>G</b>					
Symbol	Parameter	BS170	MMBF170	Units		
V <sub>DSS</sub>	Drain-Source Voltage		60	V		
V <sub>DGR</sub>	Drain-Gate Voltage ( $R_{GS} \le 1M\Omega$ )	60	V			
V <sub>GSS</sub>	Gate-Source Voltage	±	± 20			
I <sub>D</sub>	Drain Current - Continuous	500	500	mA		
	- Pulsed	1200	800			
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	- 55	- 55 to 150			
T <sub>L</sub>	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds	300				

### Thermal Characteristics T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	BS170	MMBF170	Units
P <sub>D</sub>	Maximum Power Dissipation Derate above 25°C	830 6.6	300 2.4	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	150	417	°C/W

### $\textbf{Electrical Characteristics} \ \textbf{T}_{a} = 25^{\circ} \textbf{C unless otherwise noted}$

Symbol	Parameter	Conditions	Туре	Min.	Тур.	Max.	Units
Off Charac	eteristics				I.		II.
BV <sub>DSS</sub> Drain-Source Breakdown Voltage		$V_{GS} = 0 \text{ V}, I_{D} = 100 \mu\text{A}$	All	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V	All			0.5	μΑ
I <sub>GSSF</sub>	Gate - Body Leakage, Forward	V <sub>GS</sub> = 15V, V <sub>DS</sub> = 0 V	All			10	nA
On Charac	eteristics (Notes 1)				·	•	
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 1 \text{ mA}$	All	0.8	2.1	3	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 200 \text{ mA}$	All		1.2	5	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 200 mA	BS170		320		mS
		$V_{DS} \ge 2 V_{DS(on)}, I_{D} = 200 \text{ mA}$	MMBF170		320		
Dynamic C	Characteristics				·	•	
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$	All		24	40	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz	All		17	30	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		All		7	10	pF
Switching	Characteristics (Notes 1)				·	•	
t <sub>on</sub>	Turn-On Time	$V_{DD} = 25 \text{ V}, I_{D} = 200 \text{ mA}, \\ V_{GS} = 10 \text{ V}, R_{GEN} = 25 \Omega$	BS170			10	ns
		$V_{DD} = 25 \text{ V}, I_{D} = 500 \text{ mA}, \\ V_{GS} = 10 \text{ V}, R_{GEN} = 50 \Omega$	MMBF170			10	
t <sub>off</sub>	Turn-Off Time	$V_{DD}$ = 25 V, $I_{D}$ = 200 mA, $V_{GS}$ = 10 V, $R_{GEN}$ = 25 $\Omega$	BS170			10	ns
		$V_{DD} = 25 \text{ V}, I_{D} = 500 \text{ mA},$ $V_{GS} = 10 \text{ V}, R_{GEN} = 50 \Omega$	MMBF170			10	

Note: 1. Pulse Test: Pulse Width  $\leq 300 \mu s$ , Duty Cycle  $\leq 2.0\%$ .

### **Typical Electrical Characteristics**

### BS170 / MMBF170

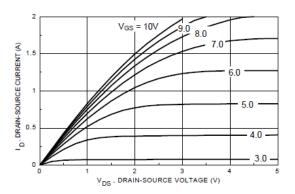


Figure 1. On-Region Characteristics.

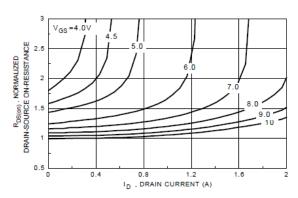


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.

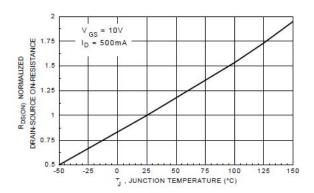


Figure 3. On-Resistance Variation with Temperature.

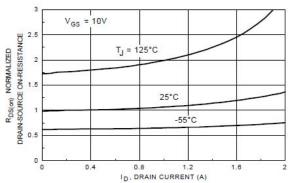


Figure 4. On-Resistance Variation with Drain Current and Temperature.

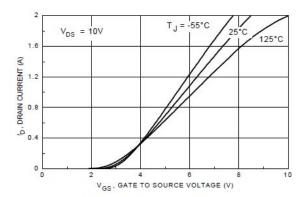


Figure 5. Transfer Characteristics.

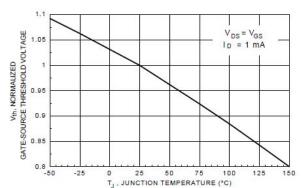


Figure 6. Gate Threshold Variation with Temperature.

### Typical Electrical Characteristics (continued)

### BS170 / MMBF170

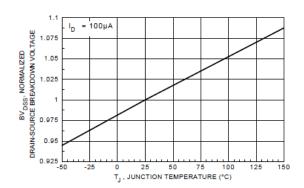


Figure 7. Breakdown Voltage Variation with Temperature.

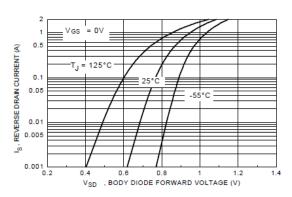


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.

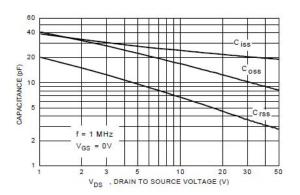


Figure 9. Capacitance Characteristics.

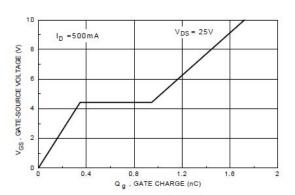


Figure 10. Gate Charge Characteristics.

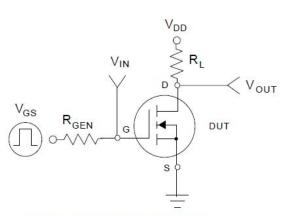


Figure 11. Switching Test Circuit.

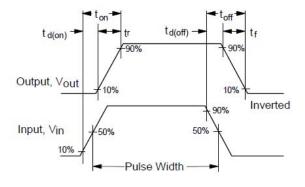


Figure 12. Switching Waveforms.

### Typical Electrical Characteristics (continued)

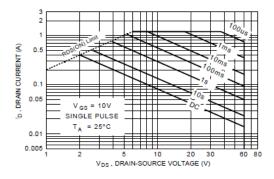


Figure 13. BS170 Maximum Safe Operating Area.

Figure 14. MMBF170 Maximum Safe Operating Area.

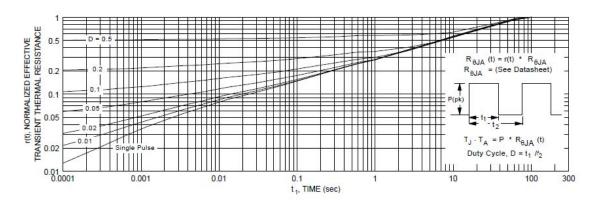


Figure 15. TO-92, BS170 Transient Thermal Response Curve.

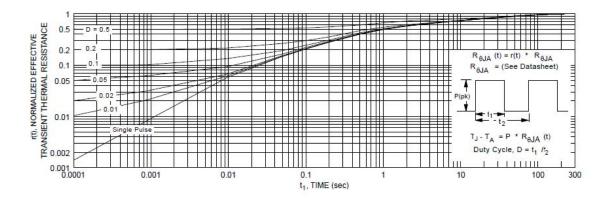
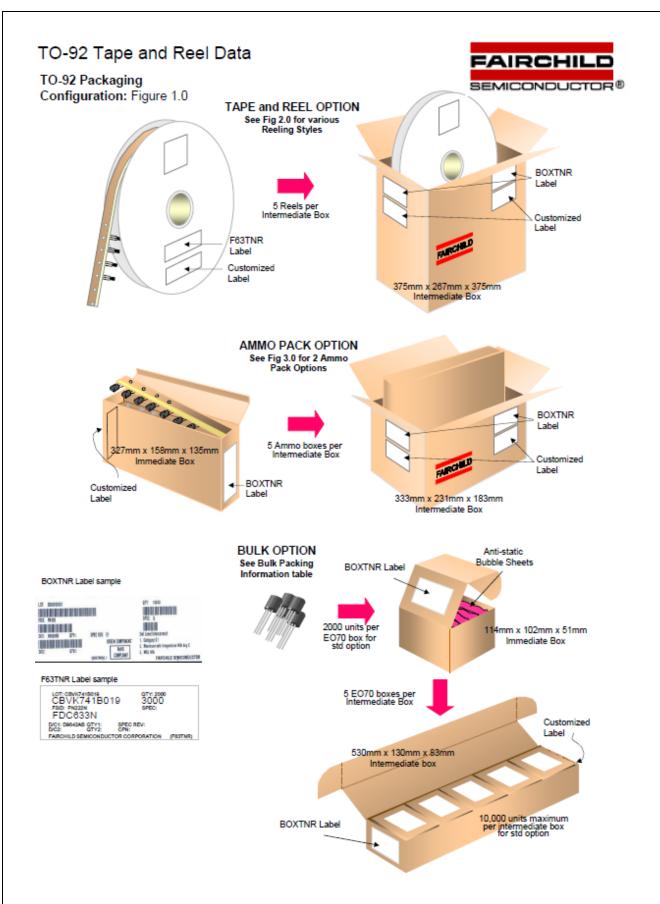


Figure 16. SOT-23, MMBF170 Transient Thermal Response Curve.



### TO-92 Tape and Reel Data, continued



TO-92 Packing Information: Figure 2.0

### TO-92 TNR/AMMO PACKING INFORMATION TABLE

Packing	Style	Quantity	EOL code
Reel	Α	2,000	D26Z
	В	2,000	D11Z
	С	2,000	D28Z
	D	2,000	D10Z
	E	2,000	D27Z
	F	2,000	D81Z
	G	2,000	D29Z
•	н	2,000	D89Z
Ammo	М	2,000	D74Z
	P	2,000	D75Z

Unit weight = 0.22 gm
Reel weight with components = 1.04 kg
Ammo weight with components = 1.02 kg
Max quantity per intermediate box = 10,000 units

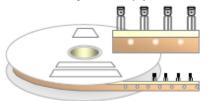
### TO-92 BULK PACKING INFORMATION TABLE

EOL CODE / FLOW OPTION	DESCRIPTION	LEADCLIP DIMENSION	MINIMUM ORDER QTY	LEADFORM OULTINE
NO EOL CODE	STRAIGHT LEADS	NO LEAD CLIP	2.0K / BOX	5
J18Z	TO-18 OPTION STD NO LEAD CLIP		2.0K / BOX	
J35Z	TO-18 OPTION REVERSE	NO LEAD CLIP	2.0K / BOX	
J05Z	TO-5 OPTION STD	NO LEAD CLIP	1.5K / BOX	
J60Z	TO-5 OPTION REVERSE	NO LEAD CLIP	1.5K / BOX	
J61Z	IN LINE 0.200 SPACING	NO LEAD CLIP	1.5K / BOX	

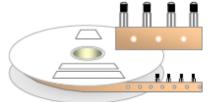
### TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 3.0

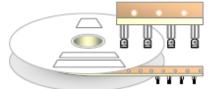




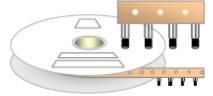
Style "A", D26Z



Style "B", D11Z

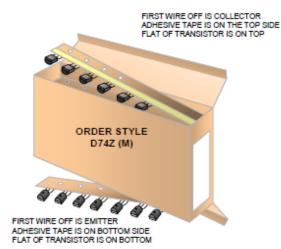


Style "C", D28Z



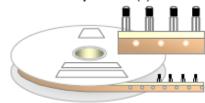
Style "D", D10Z

# TO-92 Radial Ammo Packaging Configuration: Figure 4.0

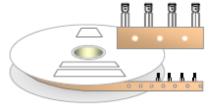




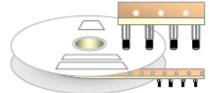
Machine Option "E" (J)



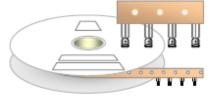
Style "E", D27Z



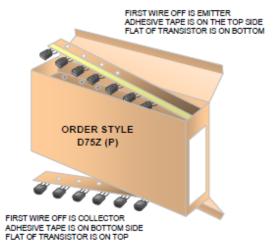
Style "F", D81Z

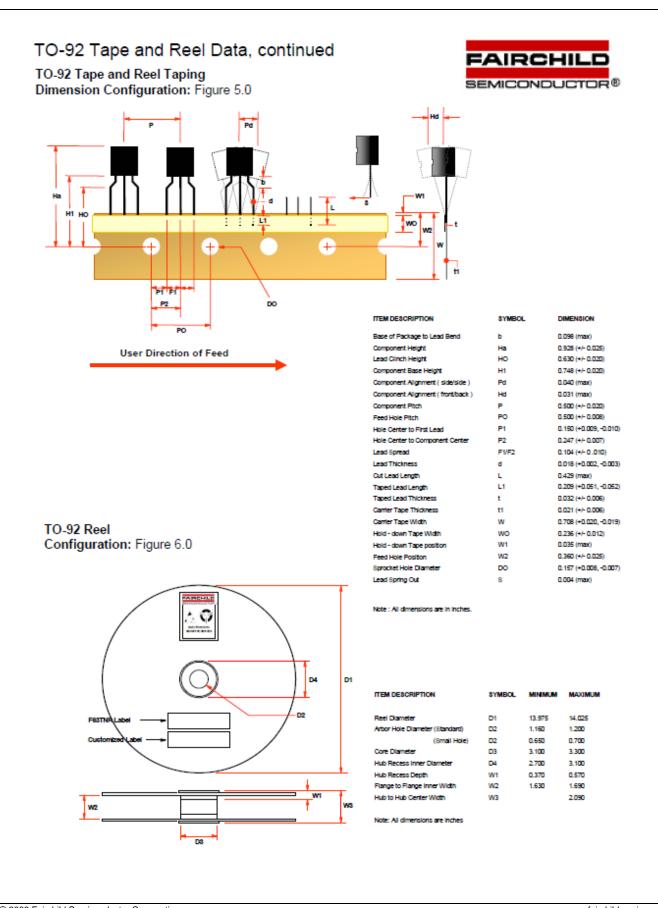


Style "G", D29Z



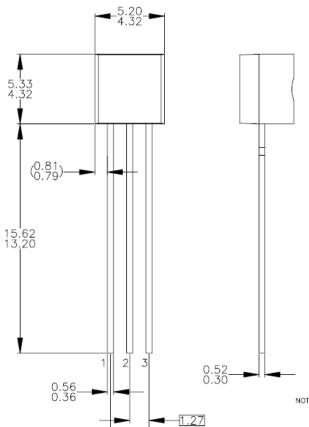
Style "H", D89Z





### Mechanical Dimensions (TO - 92)

TO - 92



NOTES: UNLESS OTHERWISE SPECIFIED

- DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS. ALL DIMENSIONS ARE IN MILLIMETERS. DRAWING CONFORMS TO ASME Y14.5M-1994. TO-92 (92,94,96,97,98) PIN CONFIGURATION:
- 96

- 1	~	J														
	O.	Р	F	М	Р	F	М	В	F	М	Р	F	М	Р	F	М
	1	Ε	S	S	Ε	S	S	В	D	G	С	G	D	С	G	D
	2	В	D	G	C	G	D	Ε	S	S	В	D	G	Ε	S	S
	3	О	G	Δ	В	D	G	С	G	D	Ε	S	S	В	D	G

### LEGEND:

P - BIPOLAR F - JFET M - DMOS E — EMITTER B — BASE C — COLLECTOR D — DRAIN S — SOURCE G — GATE

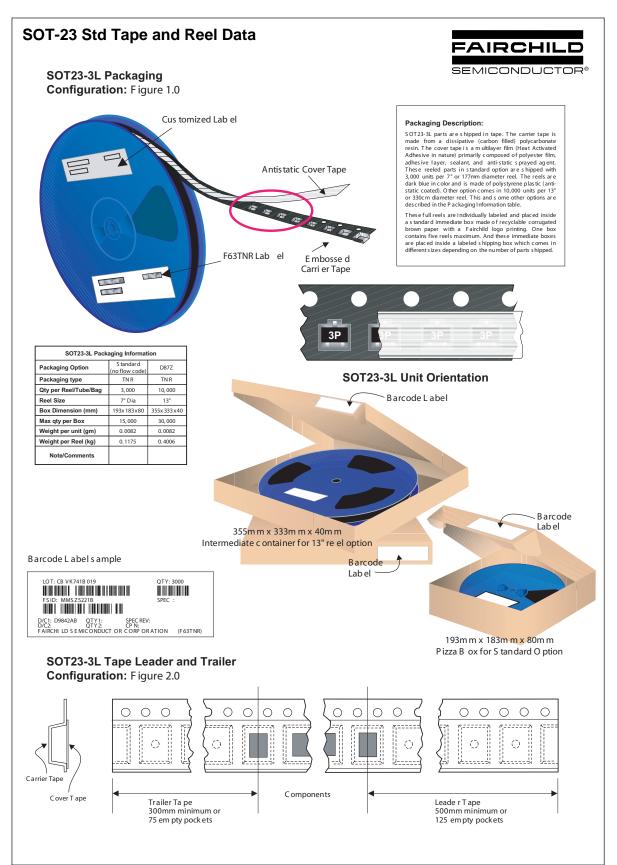
- FOR PACKAGE 92, 94, 96, 97 AND 98: PIN CONFIGURATION DRAIN "D" AND SOURCE "S" ARE INTERCHANGEAGLE AT JFET "F" OPTION. DRAWING FILENAME: MKT-ZAO3DREV3.

Dimensions in Millimeters

\_4.19 3.05

2 3

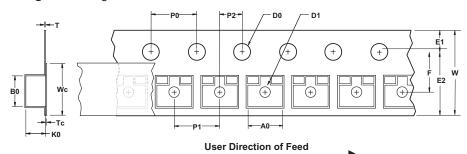
1 





### **SOT23-3L Embossed Carrier Tape**

Configuration: Figure 3.0

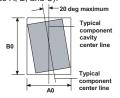


	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
<b>SOT-23</b> (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

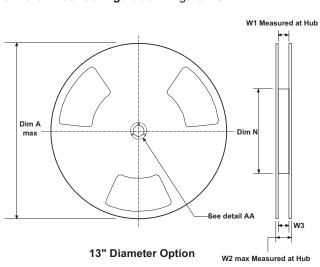


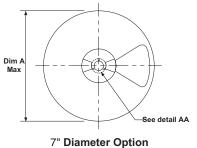
Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

### SOT23-3L Reel Configuration: Figure 4.0



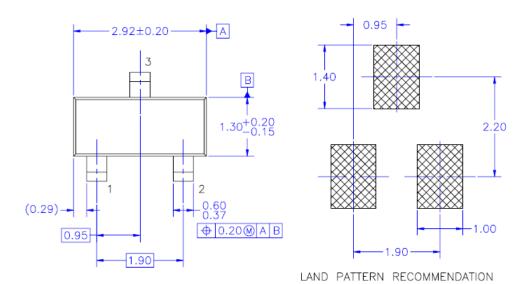


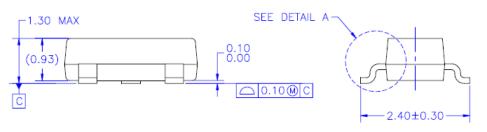
Dim D Dim C

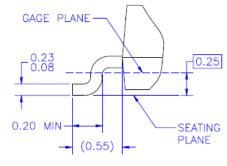
								DETAIL AA		
	Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)	
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9	
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10. 9	

### Mechanical Dimensions (SOT - 23)

## **SOT - 23**







### NOTES: UNLESS OTHERWISE SPECIFIED

- REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
  ALL DIMENSIONS ARE IN MILLIMETERS.
  DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
  DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
  DRAWING FILE NAME: MAO3DREV9

- D)

Dimensions in Millimeters





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CROSSVOLT™ Green FPS™ e-Series™

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TinyBoost™
TinyBoost™
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  expected to result in a significant injury of the user.
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### Definition of Terms

Definition of Terms									
Datasheet Identification	Product Status	Definition							
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.							
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.							
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.							
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.							

Rev. I40

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